

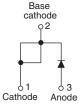
# Hyperfast Rectifier, 8 A FRED Pt®



**TO-220AC** 



TO-220 FULL-PAK





VS-8ETH06PbF

VS-8ETH06FPPbF

PRODUCT SUMMARY					
Package	TO-220AC, TO-220FP				
I <sub>F(AV)</sub>	8 A				
$V_{R}$	600 V				
V <sub>F</sub> at I <sub>F</sub>	2.4 V				
t <sub>rr</sub> typ.	18 ns				
T <sub>J</sub> max.	175 °C				
Diode variation	Single die				

### **FEATURES**

- · Hyperfast recovery time
- · Low forward voltage drop
- 175 °C operating junction temperature
- Low leakage current
- Fully isolated package (V<sub>INS</sub> = 2500 V<sub>RMS</sub>)
- UL E78996 pending
- Compliant to RoHS Directive 2002/95/EC
- Designed and qualified for industrial level



### **DESCRIPTION/APPLICATIONS**

State of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recovery time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC boost stage in the AC/DC section of SMPS, inverters or as freewheeling diodes.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Repetitive peak reverse voltage	$V_{RRM}$		600	V			
Average restified forward current	I=	T <sub>C</sub> = 144 °C	- 8 90 A				
Average rectified forward current FULL-PA	I <sub>F(AV)</sub>	T <sub>C</sub> = 108 °C					
Non repetitive peak curse ourrent		T <sub>J</sub> = 25 °C		Α			
Non-repetitive peak surge current FULL-PA	I <sub>FSM</sub>		100				
Repetitive peak forward current	I <sub>FM</sub>		16				
Operating junction and storage temperatures	T <sub>J</sub> , T <sub>Stg</sub>		- 65 to 175	°C			

<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Breakdown voltage, blocking voltage	V <sub>BR</sub> , V <sub>R</sub>	Ι <sub>R</sub> = 100 μΑ	600	-	-		
Converd velters	V	I <sub>F</sub> = 8 A	-	2.0	2.4	V	
Forward voltage	$V_{F}$	I <sub>F</sub> = 8 A, T <sub>J</sub> = 150 °C	-	1.3	1.8		
Davaraa laakaga ayuunt		V <sub>R</sub> = V <sub>R</sub> rated	-	0.3	50		
Reverse leakage current	I <sub>R</sub>	$T_J = 150$ °C, $V_R = V_R$ rated	-	55	500	μA	
Junction capacitance	C <sub>T</sub>	V <sub>R</sub> = 600 V	-	17	-	pF	
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from package body	-	8.0	-	nH	

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# VS-8ETH06PbF, VS-8ETH06FPPbF

#### Vishay Semiconductors Hyperfast Rectifier, 8 A FRED Pt®



<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>C</sub> = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS		
		$I_F = 1 A, dI_F/dt = 100$	$I_F = 1 \text{ A}, dI_F/dt = 100 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		18	22		
Payaraa raaayany tima		$I_F = 8 \text{ A}, dI_F/dt = 100$	) A/μs, V <sub>R</sub> = 30 V	-	20	25	no	
Reverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	25	-	ns	
		T <sub>J</sub> = 125 °C	$I_F = 8 \text{ A}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_R = 390 \text{ V}$	-	40	-		
Dook recovery ourrent	I <sub>RRM</sub>	T <sub>J</sub> = 25 °C		-	2.4	-	А	
Peak recovery current		T <sub>J</sub> = 125 °C		-	4.8	-		
Deviana nacevani ebena	0	T <sub>J</sub> = 25 °C		-	25	-	nC	
Reverse recovery charge	Q <sub>rr</sub>	T <sub>J</sub> = 125 °C		-	120	-	nc	
Reverse recovery time	t <sub>rr</sub>		I <sub>F</sub> = 8 A dI <sub>F</sub> /dt = 600 A/μs	-	33	-	ns	
Peak recovery current	I <sub>RRM</sub>	T <sub>J</sub> = 125 °C		-	12	-	Α	
Reverse recovery charge	Q <sub>rr</sub>		V <sub>R</sub> = 390 V	-	220	-	nC	

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		- 65	-	175	°C	
Thermal resistance,	D		-	1.4	2		
junction to case (FULL-PAK)	$R_{thJC}$		-	3.4	4.3	1	
Thermal resistance, junction to ambient per leg	R <sub>thJA</sub>	Typical socket mount	-	-	70	°C/W	
Thermal resistance, case to heatsink	R <sub>thCS</sub>	Mounting surface, flat, smooth and greased	-	0.5	-		
Mainht			-	2.0	-	g	
Weight			-	0.07	-	oz.	
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)	
Mayling daying		Case style TO-220AC	8ETH06		•		
Marking device		Case style TO-220 FULL-PAK		8ETH	106FP		

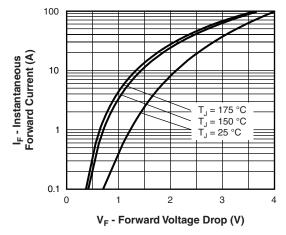


Fig. 1 - Typical Forward Voltage Drop Characteristics

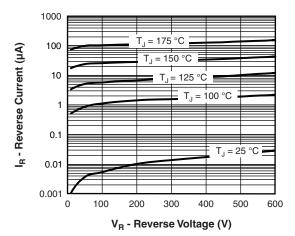


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

#### Hyperfast Rectifier, 8 A FRED Pt® Vishay Semiconductors

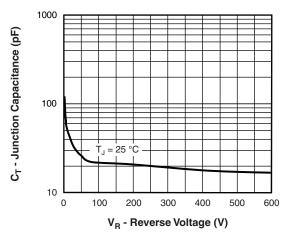


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

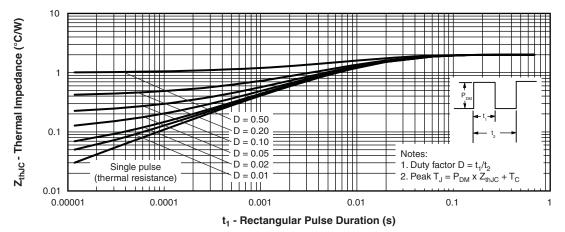


Fig. 4 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics

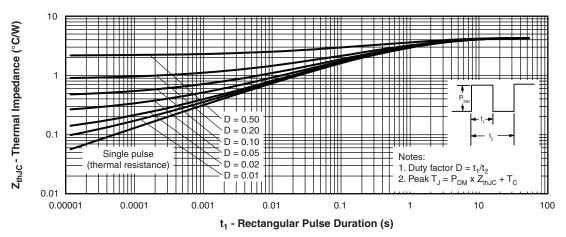


Fig. 5 - Maximum Thermal Impedance  $Z_{thJC}$  Characteristics (FULL-PAK)

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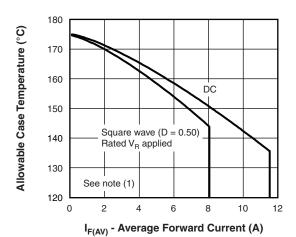


Fig. 6 - Maximum Allowable Case Temperature vs.
Average Forward Current

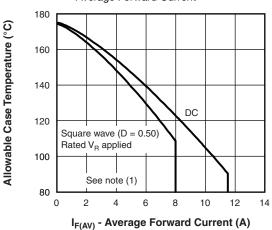


Fig. 7 - Maximum Allowable Case Temperature vs. Average Forward Current (FULL-PAK)

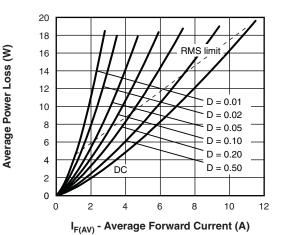


Fig. 8 - Forward Power Loss Characteristics

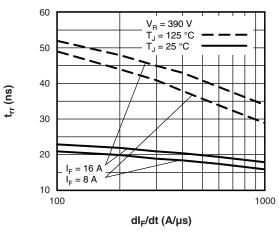


Fig. 9 - Typical Reverse Recovery Time vs.  $dI_F/dt$ 

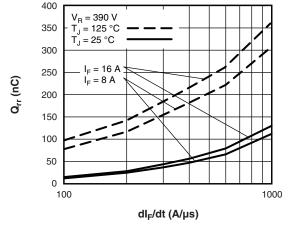


Fig. 10 - Typical Stored Charge vs. dl<sub>F</sub>/dt

#### Note

 $\begin{array}{ll} \text{(1)} & \text{Formula used: } T_C = T_J - (Pd + Pd_{REV}) \times R_{th,JC}; \\ Pd = \text{Forward power loss} = I_{F(AV)} \times V_{FM} \text{ at } (I_{F(AV)}/D) \text{ (see fig. 8)}; \\ Pd_{REV} = \text{Inverse power loss} = V_{R1} \times I_R \text{ (1 - D); } I_R \text{ at } V_{R1} = \text{Rated } V_R \\ \end{array}$ 



### Hyperfast Rectifier, 8 A FRED Pt®

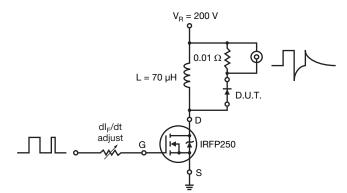
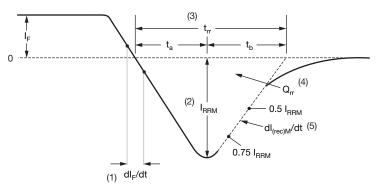


Fig. 11 - Reverse Recovery Parameter Test Circuit



- (1) dl<sub>F</sub>/dt rate of change of current through zero crossing
- (2)  $I_{RRM}$  peak reverse recovery current
- (3)  $t_{\rm rr}$  reverse recovery time measured from zero crossing point of negative going I<sub>E</sub> to point where a line passing through 0.75 I<sub>RRM</sub> and 0.50 I<sub>RRM</sub> extrapolated to zero current.
- (4)  $Q_{rr}$  area under curve defined by  $t_{rr}$ and  $I_{\text{RRM}}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5)  $dI_{(rec)M}/dt$  - peak rate of change of current during t<sub>b</sub> portion of t<sub>rr</sub>

Fig. 12 - Reverse Recovery Waveform and Definitions

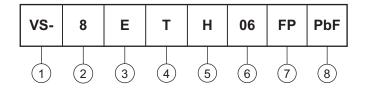
## VS-8ETH06PbF, VS-8ETH06FPPbF

Vishay Semiconductors Hyperfast Rectifier, 8 A FRED Pt®



### **ORDERING INFORMATION TABLE**

**Device code** 



Vishay Semiconductors product

Current rating (8 = 8 A)

E = Single diode

T = TO-220,  $D^2PAK$ 

H = Hyperfast recovery

Voltage rating (06 = 600 V)

• None = TO-220AC

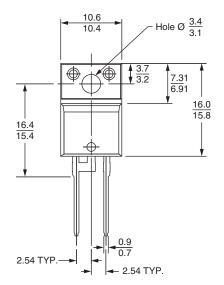
• FP = TO-220 FULL-PAK

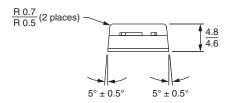
8 PbF = Lead (Pb)-free

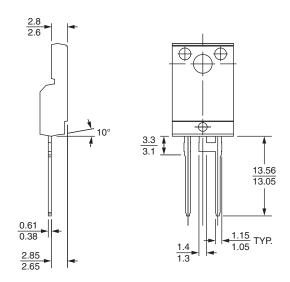
Tube standard pack quantity: 50 pieces

LINKS TO RELATED DOCUMENTS					
Dimensions	TO-220AC	www.vishay.com/doc?95221			
Dimensions	TO-220AC FULL-PAK	www.vishay.com/doc?95005			
Dort marking information	TO-220AC	www.vishay.com/doc?95224			
Part marking information	TO-220AC FULL-PAK	www.vishay.com/doc?95009			

### **DIMENSIONS** in millimeters







#### Lead assignments

Diodes

1 + 2 - Cathode

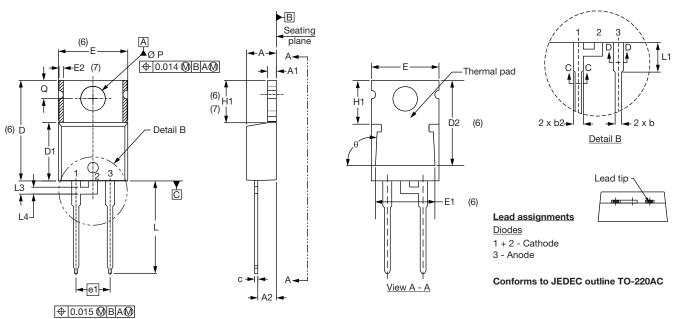
3 - Anode

Conforms to JEDEC outline TO-220 FULL-PAK



### **TO-220AC**

### **DIMENSIONS** in millimeters and inches



SYMBOL	MILLIM	IETERS	INC	NOTES	
STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.56	2.92	0.101	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.014 0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.25	0.585 0.600		3
D1	8.38	9.02	0.330	0.355	
D2	11.68	12.88	0.460 0.507		6
Е	10.11	10.51	0.398	0.414	3, 6

SYMBOL	MILLIM	IETERS	INCHES		NOTES	
STIVIBOL	MIN.	MAX.	MIN.	MAX.	NOTES	
E1	6.86	8.89	0.270	0.350	6	
E2	-	0.76	-	0.030	7	
е	2.41	2.67	0.095	0.105		
e1	4.88	5.28	0.192	0.208		
H1	6.09	6.48	0.240	0.255	6, 7	
L	13.52	14.02	0.532	0.552		
L1	3.32	3.82	0.131	0.150	2	
L3	1.78	2.13	0.070	0.084		
L4	0.76	1.27	0.030	0.050	2	
ØΡ	3.54	3.73	0.139	0.147		
Q	2.60	3.00	0.102	0.118		
θ	90° t	o 93°	90° to 93°			
		•		•	•	

#### Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3 and c1 apply to base metal only
- (5) Controlling dimension: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2 and E1
- (7) Dimension E2 x H1 define a zone where stamping and singulation irregularities are allowed
- (8) Outline conforms to JEDEC TO-220, D2 (minimum) where dimensions are derived from the actual package outline





Vishay

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